METAL-CAN TRANSISTORS

PROFESSIONAL/COMMERCIAL GRADE APPLICATION

GENERAL PURPOSE POWER TRANSISTORS IN TO-204AA PACKAGE

Device	Polarity	I_C Amp	$V_{CEO(sus)}$ Volts	h_{FE}@ min/max	I_C & Amp	V_{CE} Volts	Safe Operating Area 1 SecPulse	f_T min MHz	$R\theta_{jc}$ °C/W	P_D T_C=25°C W
2N 3055	N	15	60	20/70	4	4	2.87A × 40V	3.00	1.50	117
2N 3232	N	7.5	60	18/	3	10	—	0.02	1.50	117
2N 3442	N	10	140	20/70	3	4	—	0.80	1.50	117
2N 3771	N	30	40	15/60	15	4	3.75A × 40V	0.80	1.17	150
2N 3772	N	20	60	15/60	10	4	2.50A × 60V	0.80	1.17	150
2N 3773	N	16	140	15/60	8	4	1.50A ×100V	0.80	1.17.	150
2N 4347	N	10	120	20/70	2	4	—	—	1.50	117
2N 6253	N	15	45	20/	2	4	2.55A × 45V	—	1.50	115
2N 6257	N	20	40	15/75	8	4	3.75A × 40V	0.80	1.20	150
2N 6371	N	16	40	15/	8	4	—	—	—	117
BD 130	N	15	60	20/	4	4	2.00A × 50V	1.10	1.50	100
BD 181	N	10	45	20/70	3	4	2.90A × 40V	0.02	1.50	117
BD 182	N	15	60	20/	4	4	1.95A × 60V	0.02	1.50	117
BDW 21	N	10	45	15/150	4	4	3.00A × 30V	3.00	1.50	90
BDW 21A	N	10	60	15/150	4	4	3.00A × 30V	3.00	1.50	90
BDW 21B	N	10	80	15/150	4	4	3.00A × 30V	3.00	1.50	90
BDW 21C	N	10	100	15/150	4	4	3.00A × 30V	3.00	1.50	90
BDW 22	P	10	45	15/150	4	4	3.00A × 30V	3.00	1.50	90
BDW 22A	P	10	60	15/150	4	4	3.00A × 30V	3.00	1.50	90
BDW 22B	P	10	80	15/150	4	4	3.00A × 30V	3.00	1.50	90
BDW 22C	P	10	100	15/150	4	4	3.00A × 30V	3.00	1.50	90
BDX 18	P	15	60	20/70	4	4	3.87A × 40V	3.00	1.50	117
BDX 20	P	10	140	20/70	3	4	—	0.80	1.50	117
BDY 20	N	15	60	20/70	4	4	1.90A × 60V	1.00	1.50	115
BDY 38	N	6	40	30/	2	4	—	1.00	1.50	115
BDY 73	N	15	60	50/150	4	4	1.95A × 60V	—	1.50	—
CDP 055	P	5	50	25/100	2	2	—	4.00	1.50	50
CDN 055	N	5	50	25/100	2	2	—	4.00	1.50	50

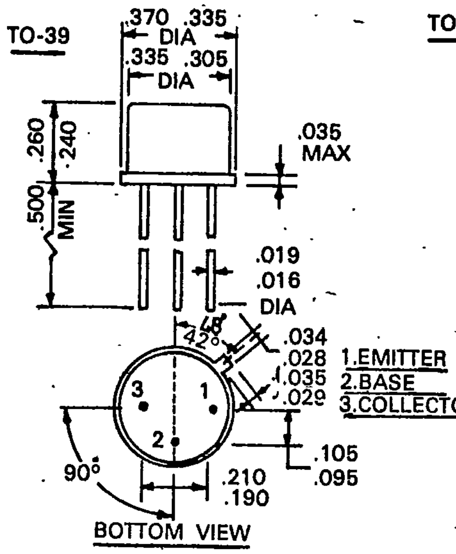
POWER SWITCHING TRANSISTORS:—

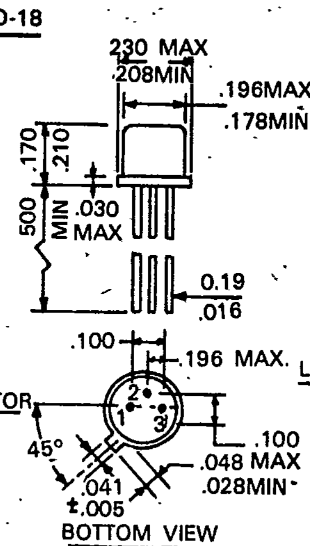
Device	Polarity	I_C Amp	V_{CEO} (sus) Volts	h_{FE} @ min/max	I_C Amp	V_{CE} Volts	t_f µs	t_s µs	f_T min MHz	$R\theta_{jc}$ °C/W	P_D T_C = 25°C W
BU 204	N	2.5	600	2.00/	2.0	5	0.75	10	7.5	2.5	10.0
BU 205	N	2.5	700	2.00/	2.0	5	0.75	10	7.5	2.5	10.0
BU 206	N	2.5	800	1.80/	2.0	5	0.75	10	7.5	1.6	10.0
BU 207	N	5.0	600	2.25/	4.5	5	0.90	10	7.0	1.6	12.5
BU 208	N	5.0	700	2.25/	4.5	5	0.70	10	7.0	1.6	12.5
BU 208D*	N	5.0	700	2.25/	4.5	5	0.70	10	7.0	1.6	12.5
BU 209	N	4.0	800	2.25/	3.0	5	0.70	10	7.0	1.6	12.5
BU 326	N	6.0	375	15.0/	2.5	10	0.50	3.5	6.0	—	60.0
BU 326A	N	6.0	400	15.0/	2.5	10	0.50	3.5	6.0	—	60.0
2N 5038	N	20	90	20.0/	12.0	5	0.50	1.5	60	1.25	140.0

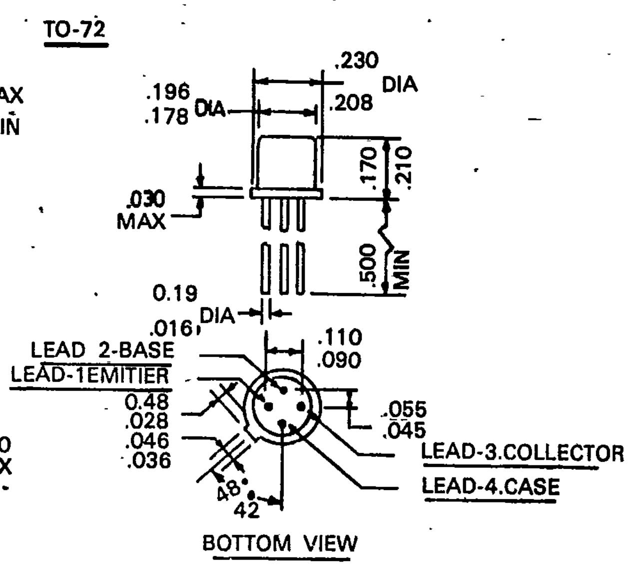
*with integrated inverse diode.

PACKAGE OUTLINES

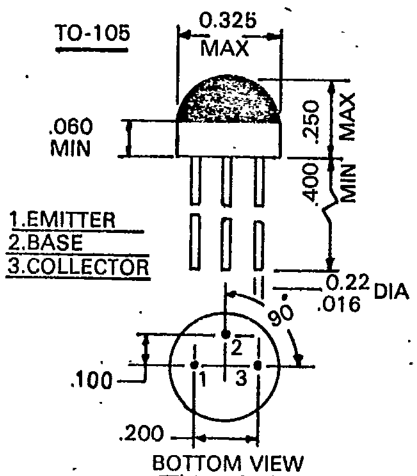
ALL DIMENSIONS IN INCHES

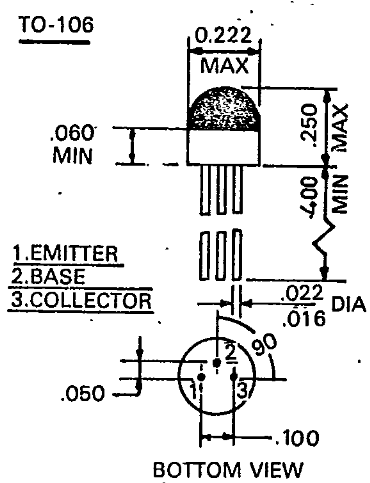


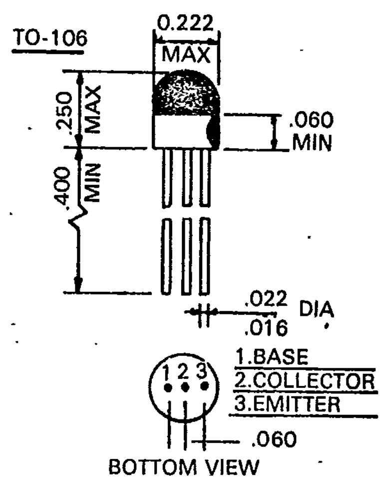




For transistor BF 167, 173 in TO-72 Package Base & Emitter leads get interchanged.



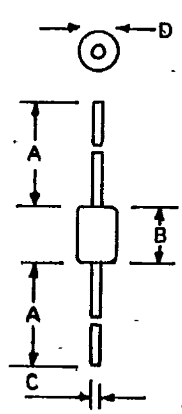




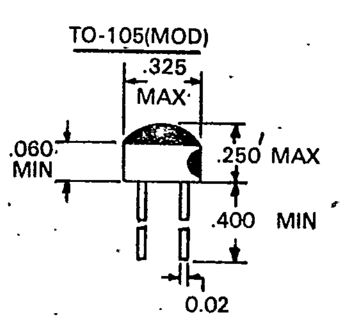
Note;For HF. transistor TO-106 Package 1.Base2.Emitter and 3. Collector

TYPICAL DIMENSIONS

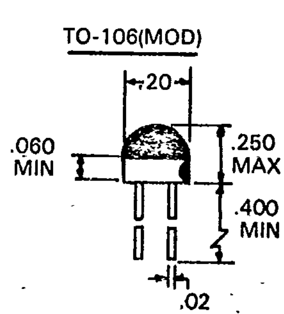
Dim	Package			
	DO-7	DO-35	DO-41	DO-34
A	1.100	1.100	1.100	1.100
B	0.230	0.140	0.150	0.104
C	0.020	0.020	0.032	0.020
D	0.096	0.070	0.94	0.056



LEAD ADJACENT TO DOT OR BAND-IS CATHODE

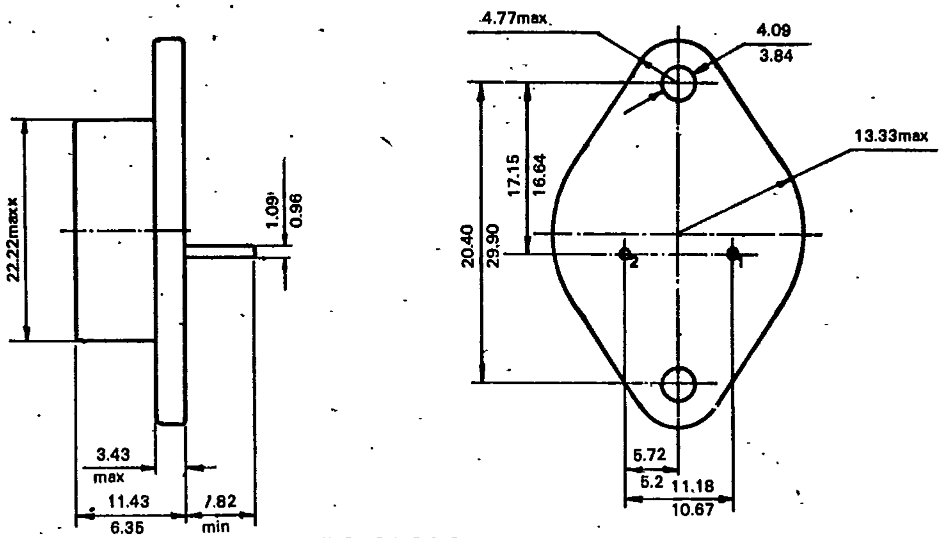


LEAD ADJACENT TO DOT IS CATHODE



LEAD ADJACENT TO DOT-IS CATHODE

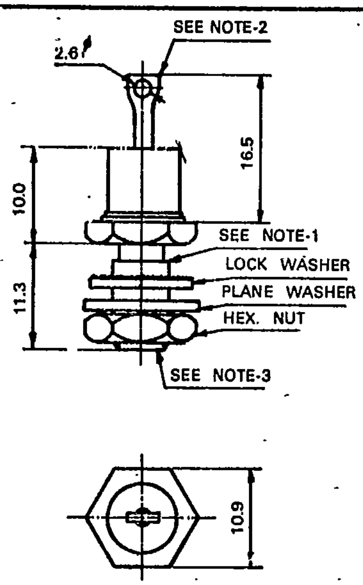
PACKAGE OUTLINES



TO-204AA

Pin Configuration: 1 :Base
2 :Emitter
Body : Collector

ALL DIMENSIONS IN M.M.

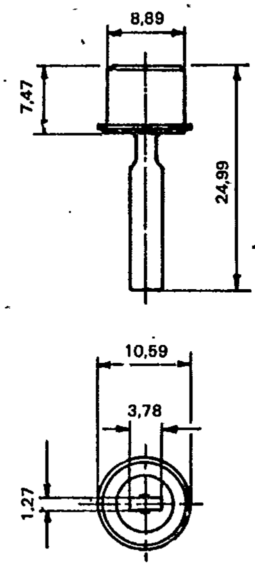


DO-4

NOTES:

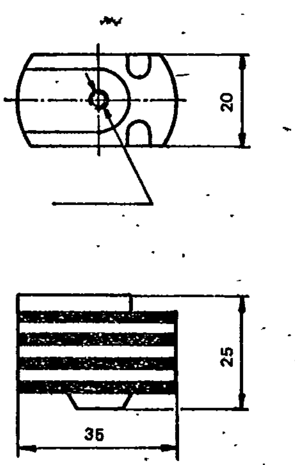
1. Threads to extend to within 2—1/2 threads of seating plane.
2. Angular orientation undefined.
3. lo-32 UNF-2A maximum pitch dia shall be (1687" 4.29 mm)

(All dimensions in mm)

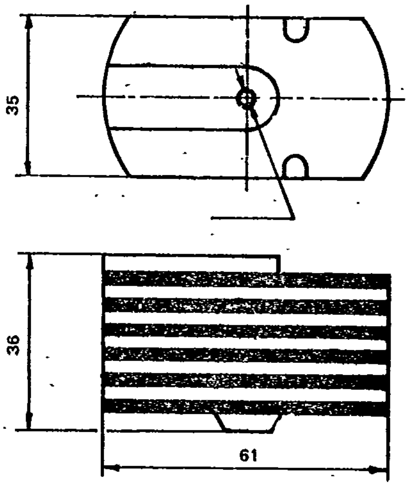


DO-21

HEAT SINK:



K 6 (3,6 AMP. DIODES)

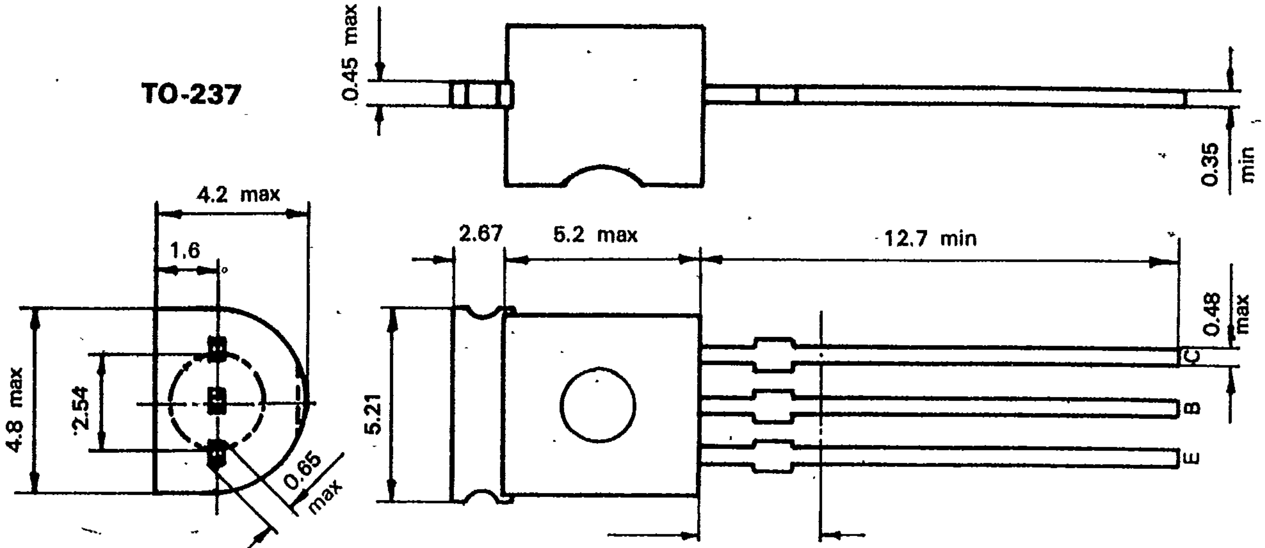


K 12 (12 AMP. DIODES)

PACKAGE OUTLINES

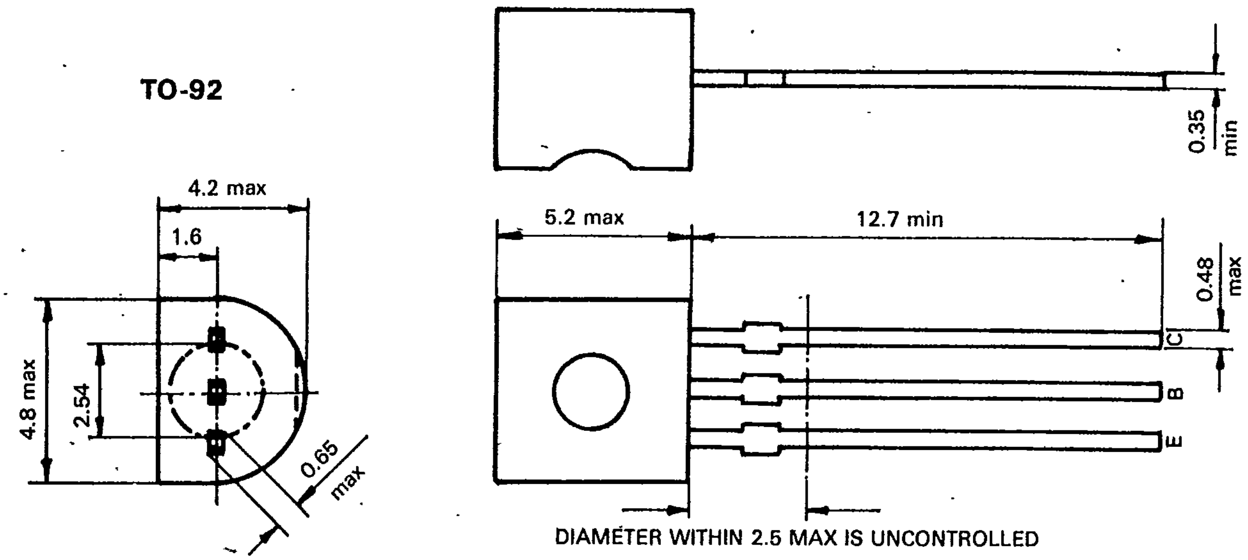
FOR TO-92 AND TO 237 PACKAGE PIN CONFIGURATION FROM LEFT TO RIGHT IS COLLECTOR-BASE-EMITTER, KEEPING FLAT FACE IN FRONT AND LEADS POINTING DOWNWARDS.

TO-237



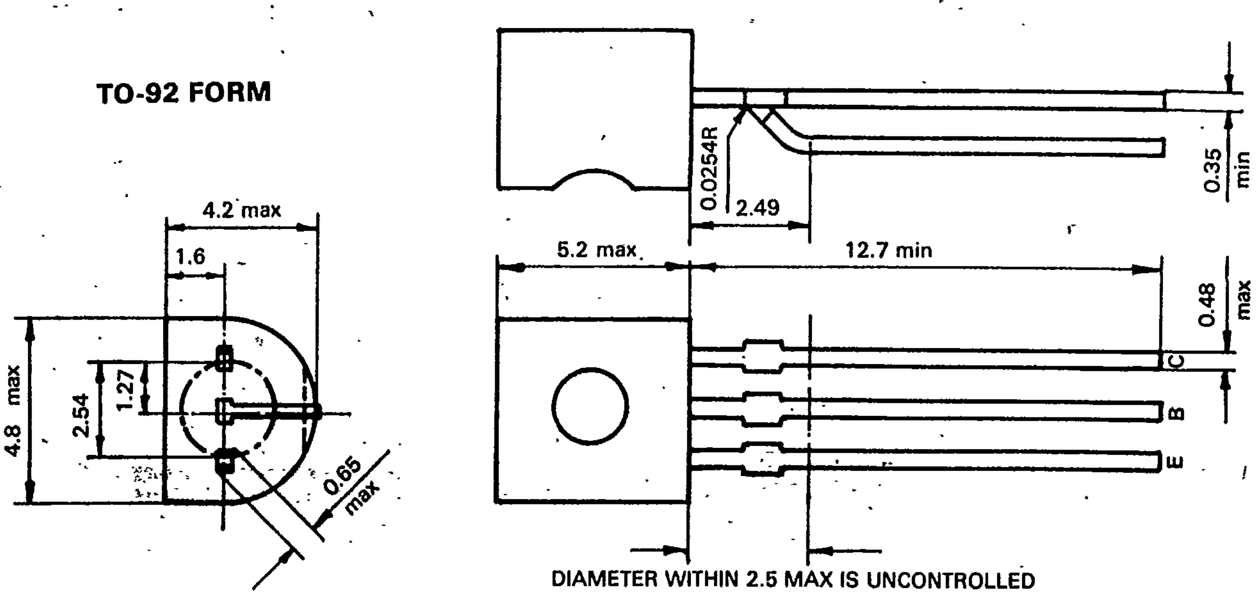
DIAMETER WITHIN 2.5 MAX IS UNCONTROLLED

TO-92



DIAMETER WITHIN 2.5 MAX IS UNCONTROLLED

TO-92 FORM



DIAMETER WITHIN 2.5 MAX IS UNCONTROLLED
ALL DIMENSIONS IN M.M.